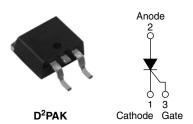


Vishay High Power Products

# Surface Mountable Phase Control SCR, 16 A



PRODUCT SUMMARY			
V <sub>T</sub> at 16 A < 1.25 V			
I <sub>TSM</sub>	300 A		
V <sub>RRM</sub>	800 to 1600 V		

#### **DESCRIPTION/FEATURES**

The 25TTS...S High Voltage Series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

Typical applications are in input rectification (soft start) and these products are designed to be used with Vishay HPP input diodes, switches and output rectifiers which are available in identical package outlines.

This product has been designed and qualified for industrial level.

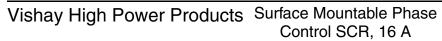
OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS SINGLE-PHASE BRIDGE THREE-PHASE BRIDGE UNITS					
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 μm) copper	3.5	5.5			
Aluminum IMS, R <sub>thCA</sub> = 15 °C/W	8.5	13.5	A		
Aluminum IMS with heatsink, R <sub>thCA</sub> = 5 °C/W	16.5	25.0			

#### Note

•  $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

PARAMETER	TEST CONDITIONS	VALUES	UNITS
I <sub>T(AV)</sub>	Sinusoidal waveform	16	Α
I <sub>RMS</sub>		25	A
V <sub>RRM</sub> /V <sub>DRM</sub>		800 to 1600	V
I <sub>TSM</sub>		300	А
V <sub>T</sub>	16 A, T <sub>J</sub> = 25 °C	1.25	V
dV/dt		500	V/µs
dI/dt		150	A/μs
T <sub>J</sub>		- 40 to 125	°C

VOLTAGE RATINGS						
PART NUMBER	V <sub>RRM</sub> , MAXIMUM PEAK REVERSE VOLTAGE V	V <sub>DRM</sub> , MAXIMUM PEAK DIRECT VOLTAGE V	I <sub>RRM</sub> /I <sub>DRM</sub> , AT 125 °C mA			
25TTS08S	800	800				
25TTS12S	1200	1200	10			
25TTS16S	1600	1600				





ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL TEST CONDITIONS		VALUES			
PARAMETER			CONDITIONS	TYP.	MAX.	UNITS
Maximum average on-state current	I <sub>T(AV)</sub>	T <sub>C</sub> = 93 °C, 180° cond	uction half sine wave	1	6	
Maximum RMS on-state current	I <sub>RMS</sub>			2	<u>.</u> 5	_
Maximum peak, one-cycle,	ı	10 ms sine pulse, rated	d V <sub>RRM</sub> applied	30	00	Α
non-repetitive surge current	I <sub>TSM</sub>	10 ms sine pulse, no v	oltage reapplied	3	50	
Maximum 124 for fusing	l <sup>2</sup> t	10 ms sine pulse, rated	d V <sub>RRM</sub> applied	450		A 2 -
Maximum I <sup>2</sup> t for fusing	i-r	10 ms sine pulse, no voltage reapplied		630	A <sup>2</sup> s	
Maximum I $^2\sqrt{t}$ for fusing	I <sup>2</sup> √t	t = 0.1 to 10 ms, no voltage reapplied		63	00	A²√s
Maximum on-state voltage drop	$V_{TM}$	16 A, T <sub>J</sub> = 25 °C		1.	25	٧
On-state slope resistance	r <sub>t</sub>	T 105 °C		12	2.0	mΩ
Threshold voltage	V <sub>T(TO)</sub>	− T <sub>J</sub> = 125 °C		1	.0	٧
Maximum various and divest leakens arrest		T <sub>J</sub> = 25 °C	V Dated V /V	0	.5	
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$V_R = Rated V_{RRM}/V_{DRM}$		1	0	
Holding current	I <sub>H</sub>	25TTS08, 25TTS12	Anode supply = 6 V,	-	100	mA
		25TTS16	resistive load, initial $I_T = 1 A$	100	150	
Maximum latching current	ΙL	Anode supply = 6 V, resistive load		20	00	
Maximum rate of rise of off-state voltage	dV/dt	500		00	V/µs	
Maximum rate of rise of turned-on current	dI/dt			15	50	A/μs

TRIGGERING					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum peak gate power	$P_{GM}$		8.0	w	
Maximum average gate power	P <sub>G(AV)</sub>		2.0	VV	
Maximum peak positive gate current	+ I <sub>GM</sub>		1.5	Α	
Maximum peak negative gate voltage	- V <sub>GM</sub>		10	V	
	I <sub>GT</sub>	Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	60	mA	
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	45		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	20		
		Anode supply = 6 V, resistive load, T <sub>J</sub> = - 10 °C	2.5		
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, T <sub>J</sub> = 25 °C	2.0	V	
to thigger		Anode supply = 6 V, resistive load, T <sub>J</sub> = 125 °C	1.0	V	
Maximum DC gate voltage not to trigger	$V_{GD}$	$T_J = 125 ^{\circ}\text{C},  V_{\text{DRM}} = \text{Rated value}$ $0.25$			
Maximum DC gate current not to trigger	I <sub>GD</sub>			mA	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	t <sub>gt</sub>	T <sub>J</sub> = 25 °C	0.9	
Typical reverse recovery time	t <sub>rr</sub>	T 105 °C	4	μs
Typical turn-off time	tq	T <sub>J</sub> = 125 °C	110	

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## Surface Mountable Phase Vishay High Power Products Control SCR, 16 A

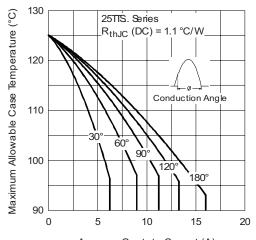
THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 40 to 125	°C
Soldering temperature	T <sub>S</sub>	For 10 s (1.6 mm from case)	240	7
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	R <sub>thJC</sub> DC operation		°C/W
Typical thermal resistance, junction to ambient (PCB mount)	R <sub>thJA</sub> (1)		40	0,11
Approximate weight			2	g
Approximate weight			0.07	oz.
			25TTS(	)8S
Marking device		Case style D <sup>2</sup> PAK (SMD-220)	25TTS1	2S
			25TTS1	6S

#### Note

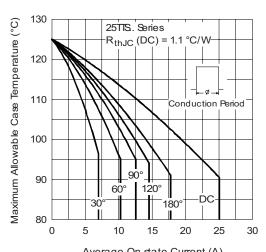
 $<sup>^{(1)}</sup>$  When mounted on 1" square (650 mm²) PCB of FR-4 or G-10 material 4 oz. (140  $\mu m]$  copper 40 °C/W For recommended footprint and soldering techniques refer to application note #AN-994

## Vishay High Power Products Surface Mountable Phase Control SCR, 16 A





Average On-state Current (A)
Fig. 1 - Current Rating Characteristics



Average On-state Current (A)
Fig. 2 - Current Rating Characteristics

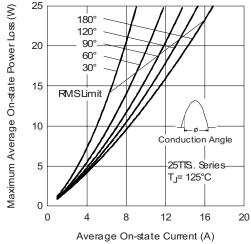


Fig. 3 - On-State Power Loss Characteristics

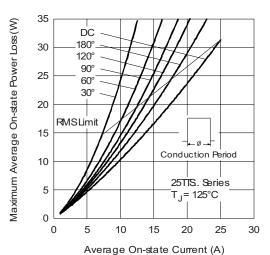
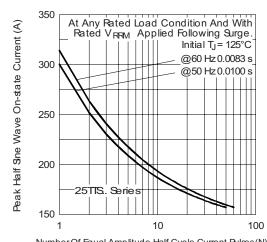


Fig. 4 - On-State Power Loss Characteristics



Number Of Equal Amplitude Half Cycle Current Pulses(N)

Fig. 5 - Maximum Non-Repetitive Surge Current

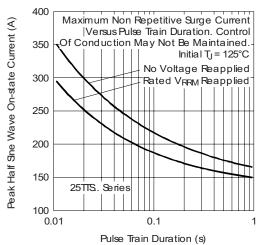


Fig. 6 - Maximum Non-Repetitive Surge Current



## Surface Mountable Phase Vishay High Power Products Control SCR, 16 A

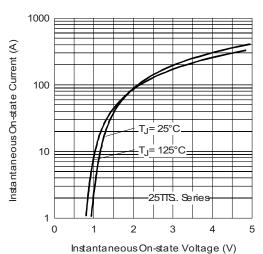
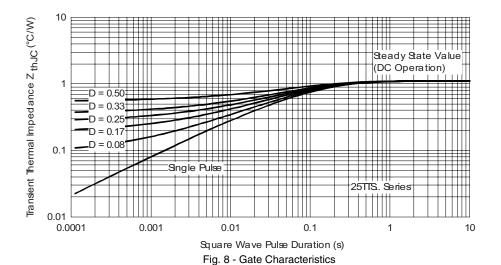


Fig. 7 - On-State Voltage Drop Characteristics



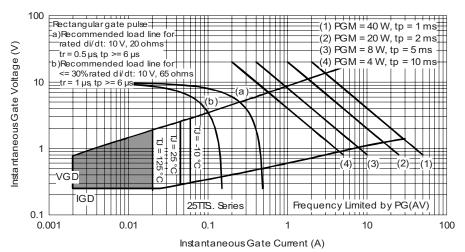
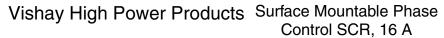


Fig. 9 - Thermal Impedance Z<sub>thJC</sub> Characteristics





#### **ORDERING INFORMATION TABLE**

Device code 25 Т Т S 16 S **TRL** (2)(3)(4) (5) (6)Current rating (25 = 25 A) Circuit configuration: T = Single thyristor Package: 3 T = TO-220AC Type of silicon: Standard recovery rectifier 08 = 800 V Voltage code x 100 = V<sub>RRM</sub> 12 = 1200 V 16 = 1600 V  $S = TO-220 D^2PAK (SMD-220) version$ • None = Tube • TRL = Tape and reel (left oriented) • TRR = Tape and reel (right oriented) 8 • None = Standard production • PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS			
Dimensions http://www.vishay.com/doc?95046			
Part marking information	http://www.vishay.com/doc?95054		
Packaging information	http://www.vishay.com/doc?95032		



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Document Number: 91000
Revision: 18-Jul-08
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